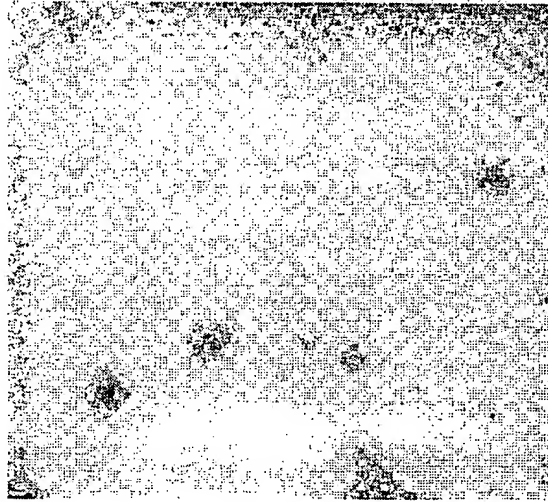




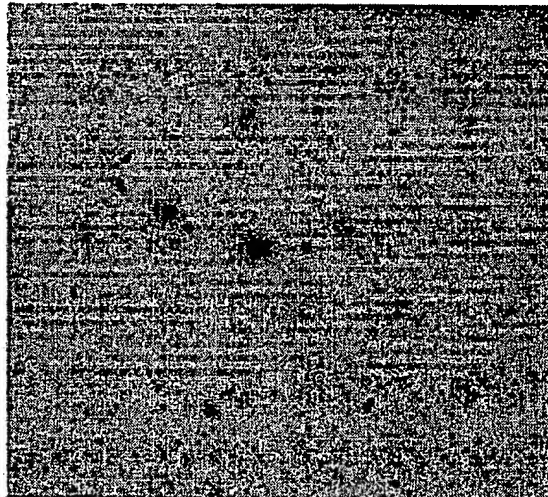
1/5

PL IMAGE OF AS-GROWN DEFECTS IN CZ Si  
SCAN AREA 1mm x 1mm



*Fig. 1*

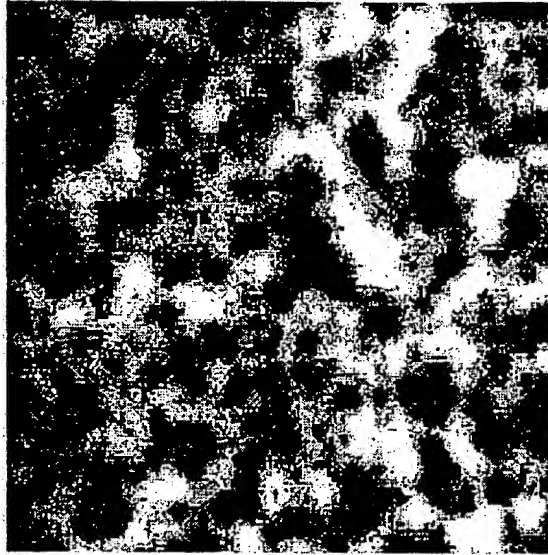
PL IMAGE OF AS-GROWN DEFECTS IN CZ Si AFTER Fe CONTAMINATION  $1 \times 10^{11}$  atoms.cm<sup>-3</sup>  
SCAN AREA 1mm x 1mm



*Fig. 2*

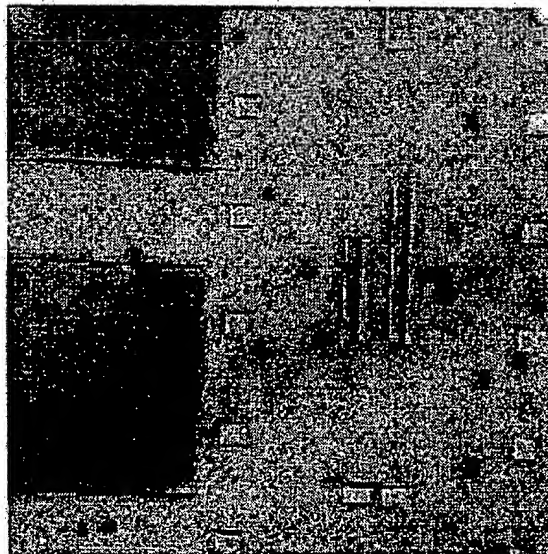
2/5

PL IMAGE OF OXYGEN PRECIPITATES IN ANNEALED Si  
SCAN AREA 1mm x 1mm



*Fig. 3*

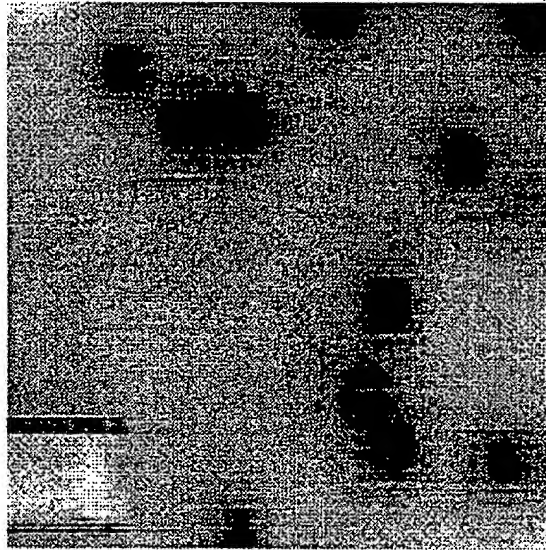
PL IMAGE OF Ni SILICIDE PRECIPITATES IN CMOS PROCESSED TEST WAFER  
SCAN AREA 500 x 500  $\mu\text{m}$



*Fig. 4*

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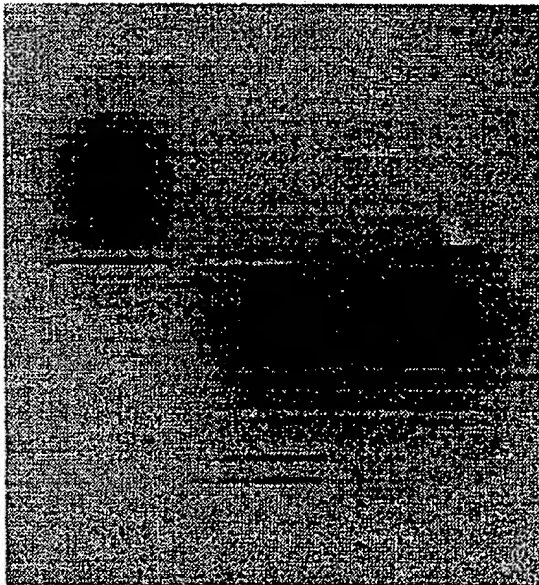
PL IMAGE OF Cu SILICIDE PRECIPITATES IN CMOS PROCESSED TEST WAFER  
SCAN AREA 100mm x 100 $\mu$ m



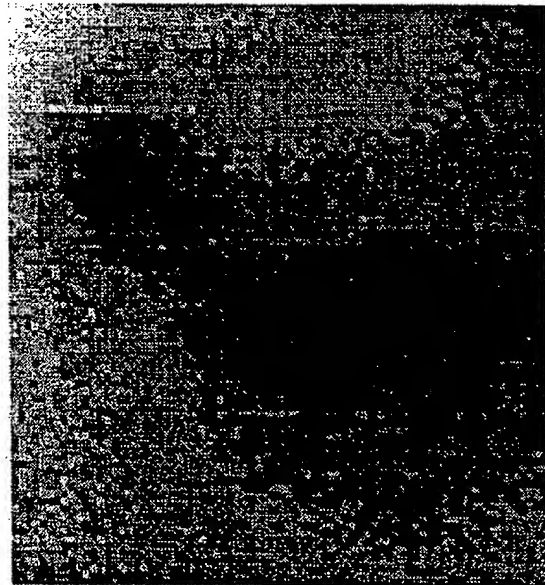
*Fig. 5*

PL IMAGE OF Cu SILICIDE PRECIPITATES IN CMOS PROCESSED TEST WAFER,  
a) HIGH INJECTION, b) LOW INJECTION.  
SCAN AREA 37 x 39  $\mu$ m

a)



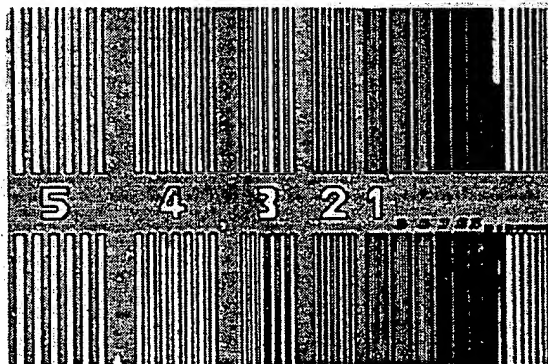
b)



*Fig. 6*

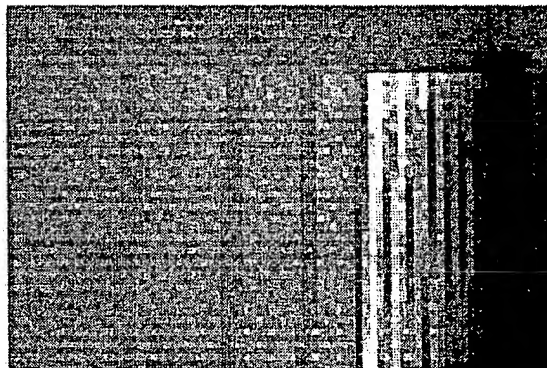
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MICROGRAPH OF LOCOS TEST STRUCTURE  
SCAN AREA 120 x 60  $\mu\text{m}$



*Fig. 7*

PL IMAGE OF LOCOS TEST STRUCTURE REVEALING A HIGH DENSITY OF DISLOCATIONS  
SCAN AREA 120 x 60  $\mu\text{m}$



*Fig. 8*

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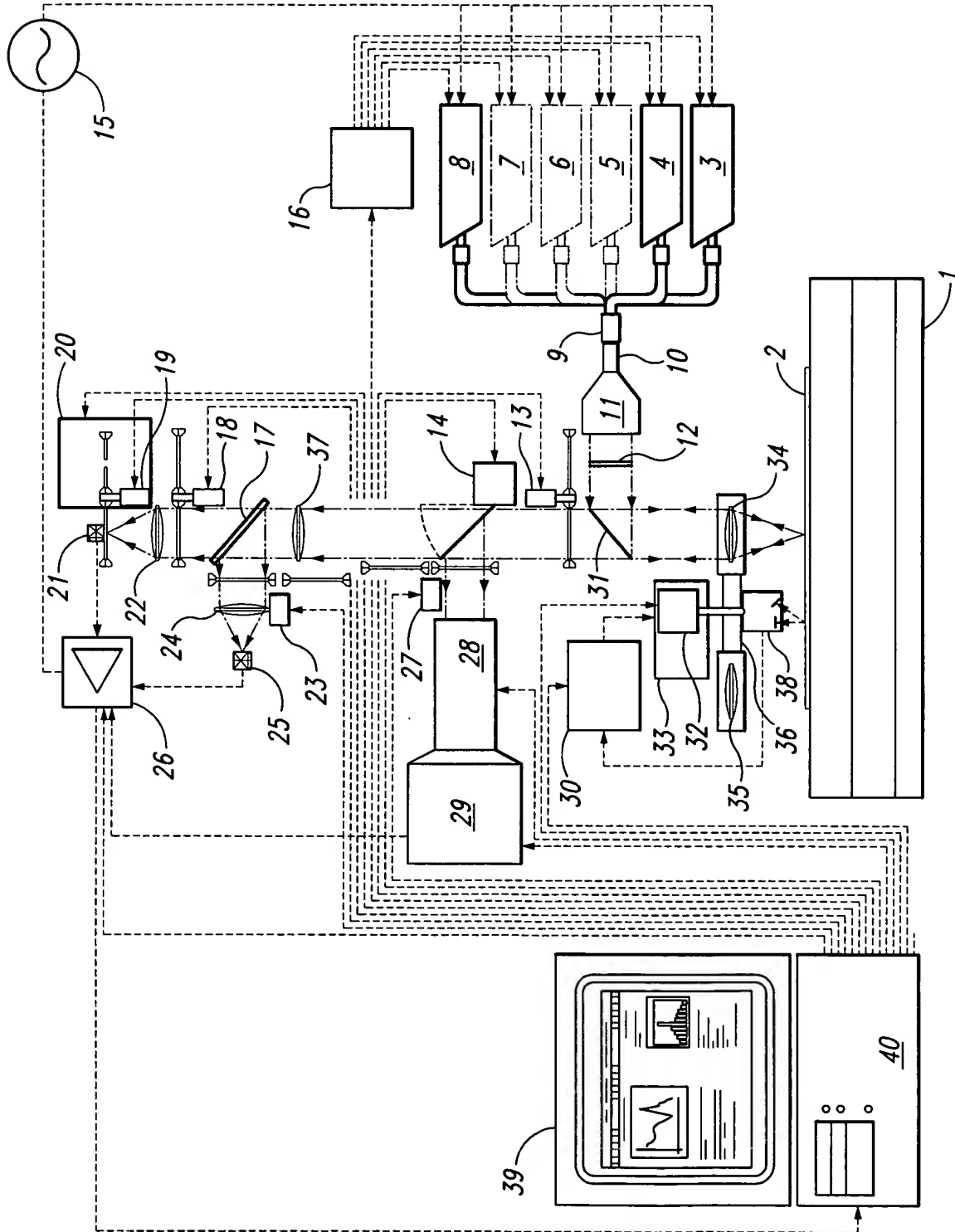


Fig. 9